

METHOD FOR FABRICATING A SEMICONDUCTOR STRUCTURE
WITH REDUCED LEAKAGE CURRENT DENSITY

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Abstract of the Disclosure

A method for fabricating a semiconductor structure including the steps of providing a silicon substrate (10) having a surface (12); forming an interface including
10 a seed layer (18) adjacent to the surface (12) of the silicon substrate (10), forming a buffer layer (20) utilizing molecular oxygen; and forming one or more layers of a high dielectric constant oxide (22) on the buffer layer (20) utilizing activated oxygen.

FIG. 4 to accompany abstract.

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